ACJP04K-800SW 4A TRIAC

Rev.A.1.0

DESCRIPTION:

The ACJP04K-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJP04K-800SW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate pin. Package TO-252 is RoHS compliant.

2 1 3 TO-252 G(3)

MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	4	A
V _{DRM} /V _{RRM}	800	V
I _{GT∏} / _Ⅲ	10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	${\mathbb C}$
Operating junction temperature range	Tj	-40-125	$^{\circ}$
Repetitive peak off-state voltage (T _j =25°C)	V _{DRM}	800	V
Repetitive peak reverse voltage (T _j =25°C)	V _{RRM}	800	V
RMS on-state current (Tc≤89°C)	I _{T(RMS)}	4	Α
Non repetitive surge peak on-state current (full cycle , t_p =20ms , T_j =25 $^{\circ}$ C)	1	45	۸
Non repetitive surge peak on-state current (full cycle , t_p =16.6ms , T_j =25 $^{\circ}$ C)	Ттѕм	49	A
I^2 t value for fusing (t_p =10ms , T_j =25°C)	l ² t	10.125	A ² s
Critical rate of rise of on-state current ($I_G=2\times I_{GT}$, f=100Hz, $T_j=125^{\circ}C$)	dl/dt	100	A/µs
Peak gate current (t₀=20μs , T¡=125℃)	Ідм	4	Α
Positive applied gate voltage	V _{GM}	15	V

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ACJP04K-800SW



Average gate power dissipation (T _j =125℃)	P _{G(AV)}	0.5	W
Peak gate power	P _{GM}	10	W
Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.8)	V _{pp}	2.75	kV

ELECTRICAL CHARACTERISTICS (T_j=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		
lgт	V _D =12V R _L =33Ω	II -III	MAX.	10	mA	
V _{GT}	VD=12V KL=3312	II -III	MAX.	1.3	V	
V _{GD}	$V_D = V_{DRM} T_j = 125^{\circ}C$ $R_L = 3.3 K\Omega$	II -III	MIN.	0.15	V	
IL	1 4 01	II	MAX.	35	mA	
IL.	IL IG=1.2IGT	III		15		
lн	I _T =100mA		MAX.	15	mA	
dV/dt	V _D =540V Gate Open	T _j =125℃	MIN.	100	V/µs	
(dl/dt)c	(dV/dt)c=10V/μs, T _j =1	25 ℃	MIN.	0.7	A/ms	
ton	Ig=20mA I _A =200mA I _R =20mA		TVD	2.5		
t _{off}	T _j =25℃		TYP.	25	μs	
VcL	I _{CL} =0.1mA t _p =1ms		MIN.	800	V	

STATIC CHARACTERISTICS

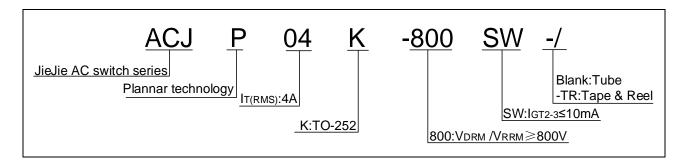
Symbol	Parameter		Value(MAX.)	Unit
Vтм	I _{тм} =5A t _p =380µs	T _j =25℃	1.55	V
Vто	Threshold voltage	T _j =125℃	0.72	V
Rd	Dynamic resistance	T _j =125℃	195	mΩ
I _{DRM}	\\-\\\-\\\-\\\-\\\-\\\-\\\\-\\\\-\\\\\-\\\\	T _j =25℃	5	μΑ
I _{RRM}	VD=VDRM VR=VRRM	T _j =125℃	0.7	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	6	°C/W
R _{th(j-a)}	junction to ambient (AC)	135	°C/W



ORDERING INFORMATION



MARKING

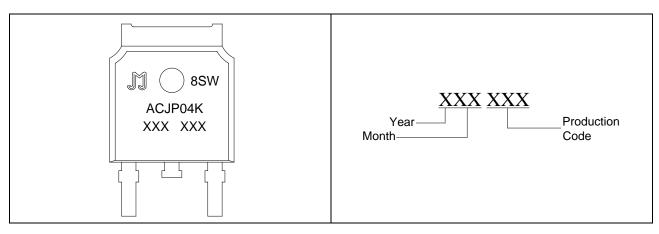


FIG.1: Maximum power dissipation versus RMS on-state current

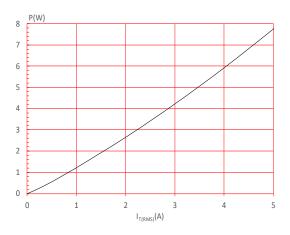


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

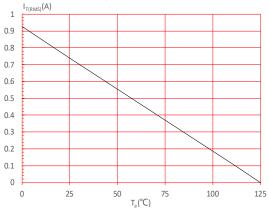


FIG.5: On-state characteristics

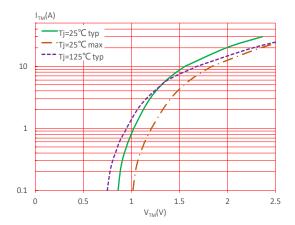


FIG.2: RMS on-state current versus case temperature

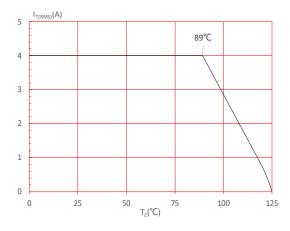


FIG.4: Surge peak on-state current versus number of cycles

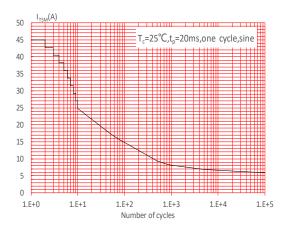


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p <20ms, and corresponding value of I^2t (dI/dt<100A/ μ s)

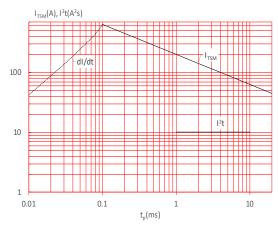


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

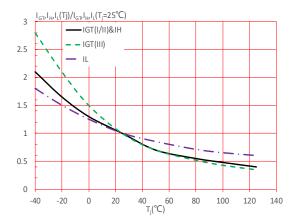
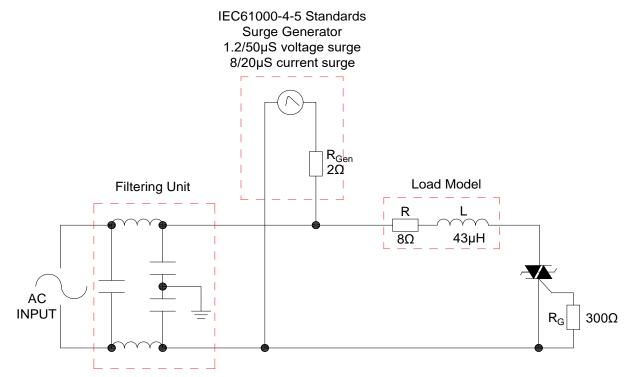
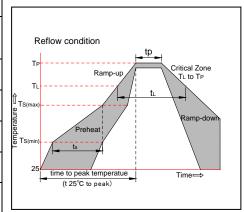


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow C	ondition	Pb-Free assembly (see figure at right)	
	-Temperature Min (T _{s(min)})	+150℃	
Pre Heat	-Temperature Max(T _{s(max)})	+200 ℃	
11001	-Time (Min to Max) (ts)	60-180 secs.	
_	ramp up rate Temp (T∟)to peak)	3℃/sec. Max	
T _{s(max)} to	T _∟ - Ramp-up Rate	3℃/sec. Max	
Defless	-Temperature(T _L)(Liquidus)	+217 ℃	
Reflow	-Temperature(t _L)	60-150 secs.	
Peak Ten	np (T _p)	+260(+0/-5) ℃	
Time with Peak Ten	nin 5°Cof actual np (t _p)	20-40secs.	
Ramp-do	wn Rate	6℃/sec. Max	
Time 25℃ to Peak Temp (T _P)		8 min. Max	
Do not ex	ceed	+260 ℃	





ORDERING INFORMATION

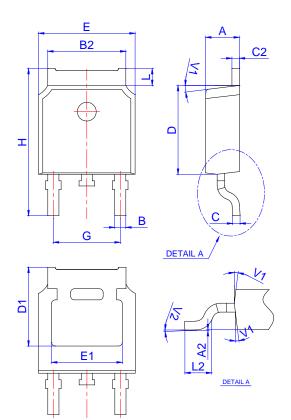
Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJP04K-800SW	900	800 10	TO-252	80	Tube
ACJP04K-800SW-TR	000				2,500

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

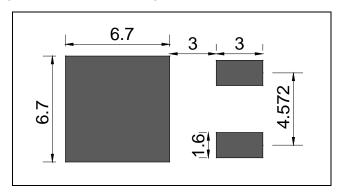


PACKAGE MECHANICAL DATA



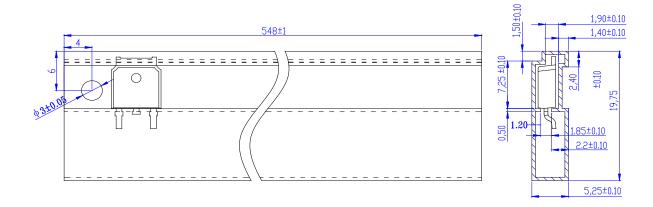
			Dime	ensions		
Ref.		Millimete	rs	Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
В	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
С	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1		5.30REF		0.209REF		=
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
Н	9.50		10.70	0.374		0.421
L	0.95		1.30	0.037		0.051
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

FOOTPRINT-TO-252 (dimensions in mm)

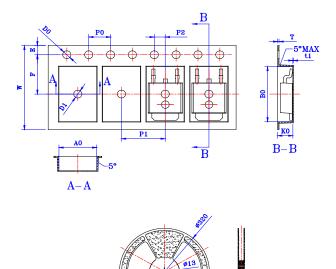




DELIVERY MODE



PACKAGE	OUTLINE	TUBE INNER BOX (PCS)		PER CARTON
TO-252	TUBE 80		4,000	20,000



	Dimensions					
Ref.	Mi	$_{ m llimete}$	rs		Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.90	7.00	0.270	0.272	0.276
В0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.106	0.109	0.113
Т	0.24	_	0.27	0.009	_	0.011
t1	0.10	_	_	0.004	_	_

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252	TAPING	2,500	25,000	13 inch



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